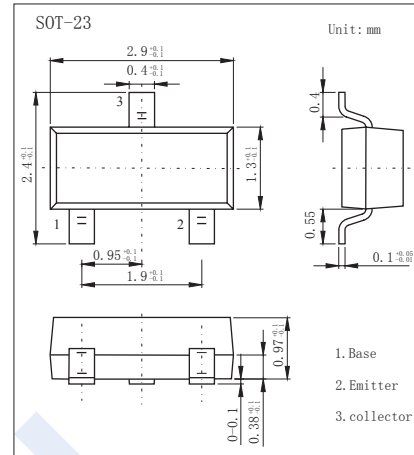


## NPN Transistors

## 2SC3265

## ■ Features

- High DC current gain
- Low saturation voltage
- Complementary to 2SA1298

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	30	V
Collector - Emitter Voltage	$V_{CE0}$	25	
Emitter - Base Voltage	$V_{EB0}$	5	
Collector Current - Continuous	$I_C$	800	mA
Base Current	$I_B$	160	
Collector Power Dissipation	$P_C$	200	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CB0}$	$I_C = 100 \mu\text{A}$ , $I_E = 0$	30			V
Collector-emitter breakdown voltage	$V_{CE0}$	$I_C = 10 \text{ mA}$ , $I_B = 0$	25			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = 100 \mu\text{A}$ , $I_C = 0$	5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = 30 \text{ V}$ , $I_E = 0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = 5 \text{ V}$ , $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 \text{ mA}$ , $I_B = 20 \text{ mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500 \text{ mA}$ , $I_B = 20 \text{ mA}$		0.72	1	
Base - emitter voltage	$V_{BE}$	$V_{CE} = 1 \text{ V}$ , $I_C = 10 \text{ mA}$	0.5		0.8	
DC current gain	$h_{FE}$	$V_{CE} = 1 \text{ V}$ , $I_C = 100 \text{ mA}$	100		320	
		$V_{CE} = 1 \text{ V}$ , $I_C = 800 \text{ mA}$	40			
Collector output capacitance	$C_{ob}$	$V_{CB} = 10 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$		13		pF
Transition frequency	$f_T$	$V_{CE} = 5 \text{ V}$ , $I_C = 10 \text{ mA}$		120		MHz

■ Classification of  $h_{FE(1)}$ 

Marking	EO	EY
Range	100-200	160-320

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■ Typical Characteristics

